

TSC5303D

High Voltage NPN Transistor with Diode



TO-251 (IPAK) TO-252 (DPAK)



Pin Definition:

- 1. Base
- Collector
 Emitter

PRODUCT SUMMARY

BV _{CEO}	400V
BV _{CBO}	700V
Ic	3A
V _{CE(SAT)}	0.17V @ I _C =1A, I _B =0.25A

Features

- Build-in Free-wheeling Diode Makes Efficient Antisaturation Operation
- No Need to Interest an h_{FE} Value Because of Low Variable Storage-time Spread Even Though Comer Spirit Product.
- Low Base Drive Requirement
- Suitable for Half Bridge Light Ballast Application

Structure

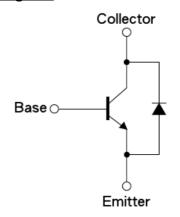
- Silicon Triple Diffused Type
- NPN Silicon Transistor
- Integrated Anti-parallel Collector-Emitter Diode

Ordering Information

Part No.	Package	Packing		
TSC5303DCP ROG	TO-252	2.5kpcs / 13" Reel		
TSC5303DCH C5G	TO-251	75pcs / Tube		

Note: "G" denotes Halogen Free Products

Block Diagram



Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Collector-Base Voltage	V _{CBO}	700	V	
Collector-Emitter Voltage @ V _{BE} =0V	V _{CES}	700	V	
Collector-Emitter Voltage	V _{CEO}	400	V	
Emitter-Base Voltage	V _{EBO}	9	V	
Collector Current	I _C	3	А	
Collector Peak Current (tp <5ms)	Ісм	6	А	
Base Current	I _B	1.5	А	
Base Peak Current (tp <5ms)	I _{BM}	3	А	
Power Total Dissipation @ T _C =25°C	P _{DTOT}	30	W	
Maximum Operating Junction Temperature	T _J	+150	°C	
Storage Temperature Range	T _{STG}	-55 to +150	°C	



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Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ _{JC}	4.15	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	75	°C/W

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	I _C =1mA, I _B =0	BV _{CBO}	700			V
Collector-Emitter Breakdown Voltage	I _C =10mA, I _E =0	BV _{CEO}	400			V
Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	BV_{EBO}	9			V
Collector Cutoff Current	V _{CB} =700V, I _E =0	I _{CBO}			10	μA
Collector Cutoff Current	V _{CE} =400V, I _B =0	I _{CEO}			10	μA
Emitter Cutoff Current	V _{EB} =7V, I _C =0	I _{EBO}			10	μA
Collector-Emitter Saturation Voltage	I _C =0.4A, I _B =0.1A	V _{CE(SAT)1}		0.10	0.7	V
	I _C =1A, I _B =0.25A	V _{CE(SAT)2}		0.17	1	
	I _C =2A, I _B =0.5A	V _{CE(SAT)3}		0.55		
Base-Emitter Saturation Voltage	I _C =1A, I _B =0.25A	V _{BE(SAT)1}			1.1	V
	I _C =2A, I _B =0.5A	V _{BE(SAT)2}			1.2	
DC Current Gain	V_{CE} =5V, I_C =10mA	h _{FE}	10			
	V _{CE} =5V, I _C =1A		15		30	
	V _{CE} =5V, I _C =2A		5			
Forward Voltage Drop	I _F =2A	Vf			2	V
Turn On Time	V _{CC} =250V, I _C =1A,	t _{ON}		0.2	0.6	μs
Storage Time	$I_{B1}=I_{B2}=0.2A$, $t_p=25\mu s$	t _{STG}		2.7	4.5	μs
Fall Time	Duty Cycle<1%	t _f		0.16	0.3	μs

Note: Pulsed duration =380µs, duty cycle ≤2%





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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. Static Characteristics 5.0 Ic[A], Collector Current 4.0 lb=900mA Ib=800mA Ib=700mA b=600mA 3.0 lb=500mA lb=400mA lb=300mA 2.0 lb=200mA lb=100mA lb=10mA 0 Vce[V], Collector-Emitter Voltage

Figure 3. Vce(sat) v.s. Vbe(sat)

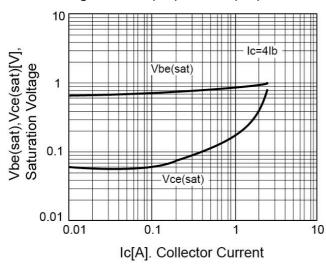


Figure 5. Reverse Bias SOA

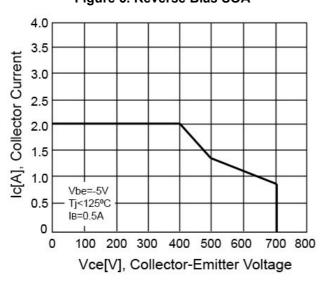


Figure 2. DC Current Gain

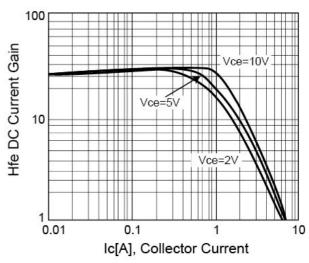


Figure 4. Power Derating

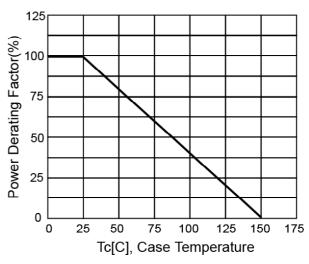
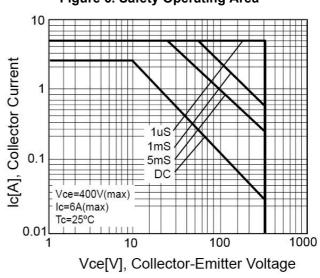


Figure 6. Safety Operating Area

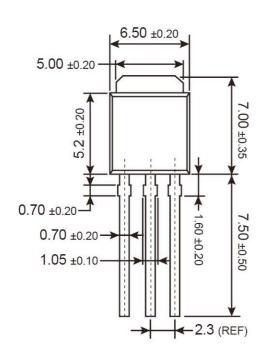


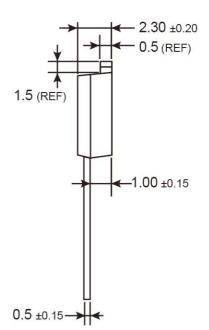




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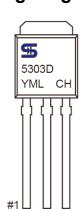
TO-251 Mechanical Drawing





Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

4/6

L = Lot Code

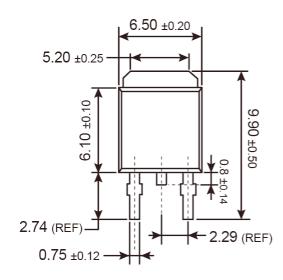
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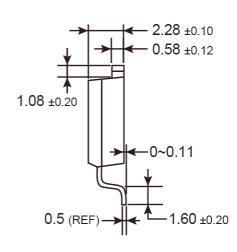




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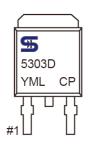
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